In th Sp cification

Replace the Abstract on p. 27 with the paragraph shown below:

ABSTRACT OF THE DISCLOSURE

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Semiconductor processing methods of forming transistors, semiconductor processing methods of forming dynamic random access memory circuitry, and related integrated circuitry are described. In one embodiment, active areas are formed over a substrate, with one of the active areas having a width of less than one micron, and with some of the active areas having different widths. A gate line is formed over the active areas to provide transistors having different threshold voltages. In one embodiment, the transistors are provided with different threshold voltages without using a separate channel implant for the transistors.

In the Claims

1. A semiconductor processing method of forming transistors comprising:

forming a plurality of shallow trench isolation regions received within a substrate, the shallow trench isolation regions being formed to define a plurality of active areas having widths within the substrate, some of the widths being no greater than about one micron, at least two of the widths being different; and

forming a gate line over respective active areas to provide individual transistors, the transistors corresponding to the active areas having the different widths having different threshold voltages.